Features

- Halogen Free. “Green” Device (Note 1)
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

PNP
Plastic Encapsulate Transistor

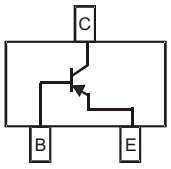
Maximum Ratings

- Operating Junction Temperature Range: -55℃ to +150℃
- Storage Temperature Range: -55℃ to +150℃
- Thermal Resistance: 625℃/W Junction to Ambient

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-160	V
Collector-Emitter Voltage	V_{CEO}	-150	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-200	mA
Collector Power Dissipation	P_C	200	mW

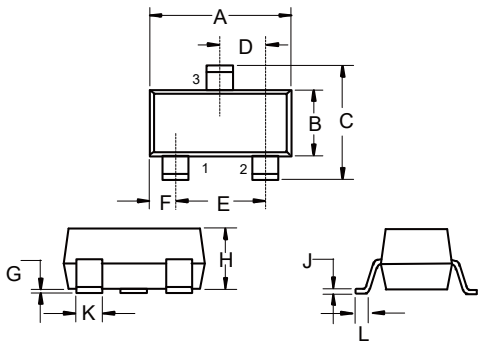
Note: 1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Internal Structure



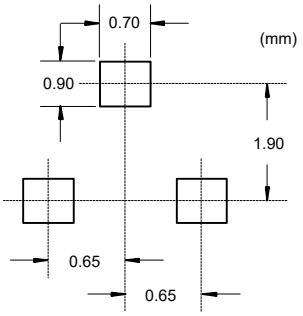
Marking: K4M

SOT-323



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.071	0.087	1.80	2.20	
B	0.045	0.053	1.15	1.35	
C	0.083	0.096	2.10	2.45	
D	0.026		0.65		TYP.
E	0.047	0.055	1.20	1.40	
F	0.012	0.016	0.30	0.40	
G	0.000	0.004	0.00	0.10	
H	0.035	0.044	0.90	1.10	
J	0.002	0.010	0.05	0.25	
K	0.006	0.016	0.15	0.40	
L	0.010	0.018	0.26	0.46	

Suggested Solder Pad Layout



Electrical Characteristics @ 25°C Unless Otherwise Specified

Parameter	Symbol	Min	Typ	Max	Units	Conditions
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-160			V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-150			V	I_C=-1mA, I_B=0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	I_E=-10μA, I_C=0
Collector-Base Cutoff Current	I_{CBO}			-50	nA	V_{CB}=-120V, I_E=0
Emitter-Base Cutoff Current	I_{EBO}			-50	nA	V_{EB} =-3V, I_C=0
DC Current Gain	$h_{FE(1)}$	50				V_{CE}=-5V, I_C=-1mA
	$h_{FE(2)}$	60		300		V_{CE}=-5V, I_C=-10mA
	$h_{FE(3)}$	50				V_{CE}=-5V, I_C=-50mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.2	V	I_C=-10mA, I_B=-1mA
				-0.5	V	I_C=-50mA, I_B=-5mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1	V	I_C=-10mA, I_B=-1mA
				-1	V	I_C=-50mA, I_B=-5mA
Transition Frequency	f_T	100		300	MHz	V_{CE}=-10V, I_C=-10mA, f=100MHz
Output Capacitance	C_{ob}			6	pF	V_{CB}=-10V, I_E=0, f=1MHz
Noise Figure	NF			8	dB	V_{CE}=-5V, I_C=-200μA, R_g=10Ω f=1KHz

Curve Characteristics

Fig. 1 - Static Characteristics

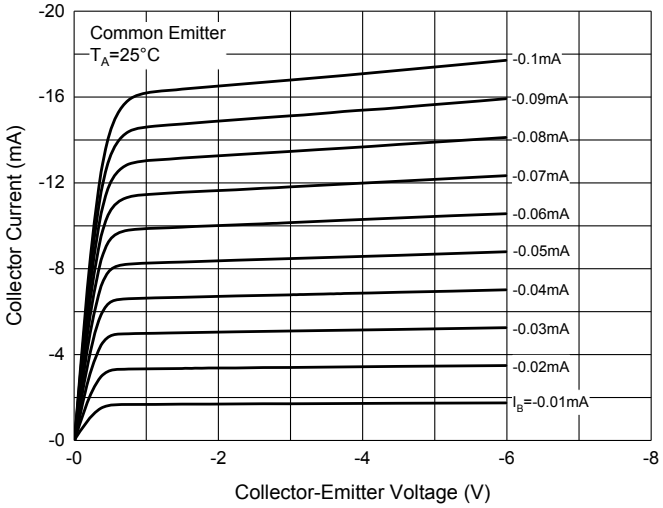


Fig. 2 - DC Current Gain Characteristics

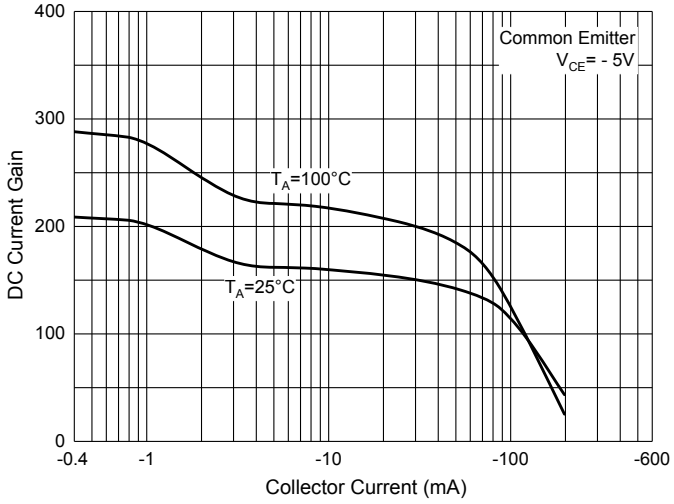


Fig. 3 - Base-Emitter Saturation Voltage Characteristics

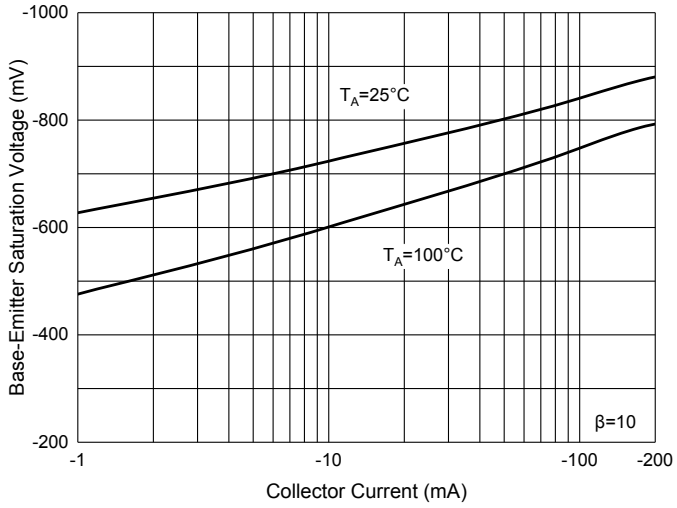


Fig. 4 - Collector-Emitter Saturation Voltage Characteristics

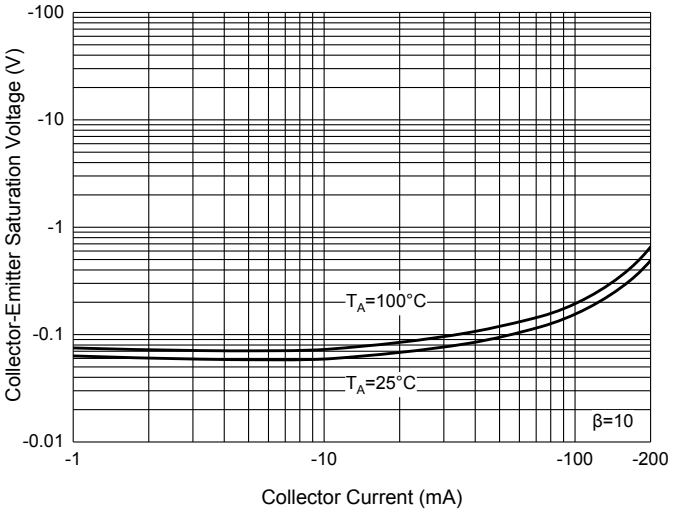


Fig. 5 - Base-Emitter Voltage Characteristics

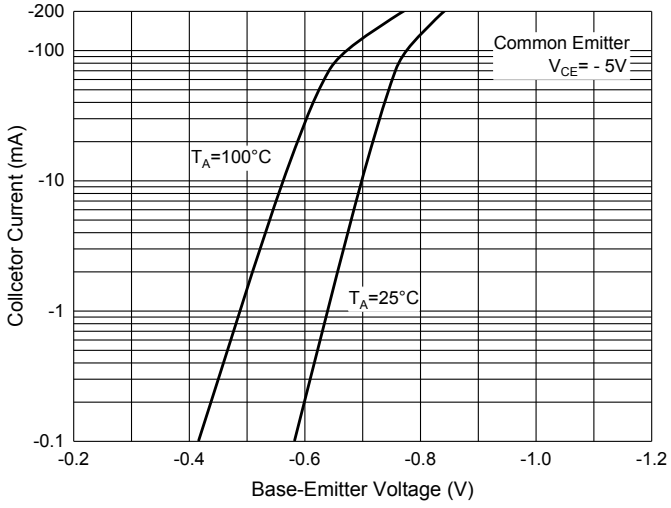
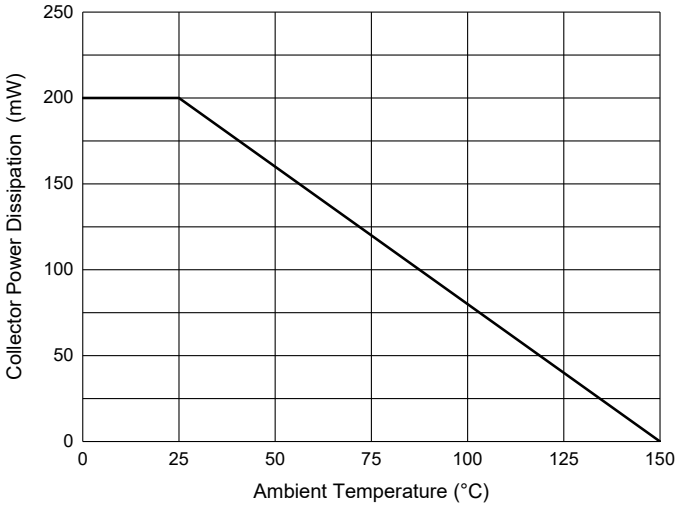


Fig. 6 - Collector Power Derating Curve



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel: 3Kpcs/Reel